POGORMIOV, I.D., inzh.: ZEMSKOV, P.I., kand.tekhn.nauk

Cold electric-arc welding of cast iron. Izv.vys.ucheb. zav.; mashinostr. no.2:146-152 59. (MIRA 13:3)

1. Khar'kovskiy institut inshenerov kommunal'nogo stroitel'stva i Khar'kovskiy zavod "Serp i molot". (Electric welding)

ZEMSKOV, Pavel Ivanovich; YAKUSHINA, Yelena Nikolayevna;

KHAKCHENKO, Yevgeniy Nikolayevich; ZUBENKO, I.F., dots.,

otv. red.; ALYAB'YEV, N.Z., red.

[Materials and coatings for the piston rings of motor-vehicle and tractor engines] Materialy i pokrytiia porshnevykh kolets avtotraktornykh dvigatelei. Khar'kov, Izdvo Khar'kovskogo univ., 1963. 129 p. (MIRA 17:8)

ZEMSKOV, P.I.; YAKUSHINA, Ye.N.

Antifriction pseudoalloys for engine bearings. Avt. prom. 29 no.7:21-23 Jl 163. (MIRA 16:8)

1. Khar'kovskiy traktornyy zavod.
(Bearing metals)

ZEMSKOV, P.I., kand. tekhn. nauk; YAKUSHINA, Ye.N., inzh.

Using pseudoalloys as substitutes for bronzes and babbitts.

Mashinostroenie no.3:110 My-Je '63. (MIRA 16:7)

1. Khar'kovskiy traktornyy zavod.

(Powder metallurgy)

ZEMSKOV, P.I., inzh.; POCORELOV, I.D., inzh.; YAKUSHINA, Ye.N., inzh.; KHARCHENKO, Ye.N., inzh.

Welding and soldering during the repair of AL10V aluminum alloy parts. Svar. proizv. no.8:40-41 Ag '63. (MIRA 17:1)

1. Khar'kovskiy zavod "Serp i molot".

ZEMSKOV, P.I., dotsent; POGORELOV, I.D.; YAKUSHIMA, Ye.N.

Soldering aluminum parts. Mashinostroitel' no.7:38-39 Jl '62.

(Aluminum Welding)

(Aluminum Welding)

ZEMSKOV, P.I., kand.tekhn.nauk, dotsent; POGORELOV, I.D., inzh.; BALYUK, B.K., inzh.

Investigating the performance of engine bimetallic bushings made with ASM alloy. Izv.vys.ucheb.zav.; mashinostr. no.11:79-83 '61. (MIRA 14:12)

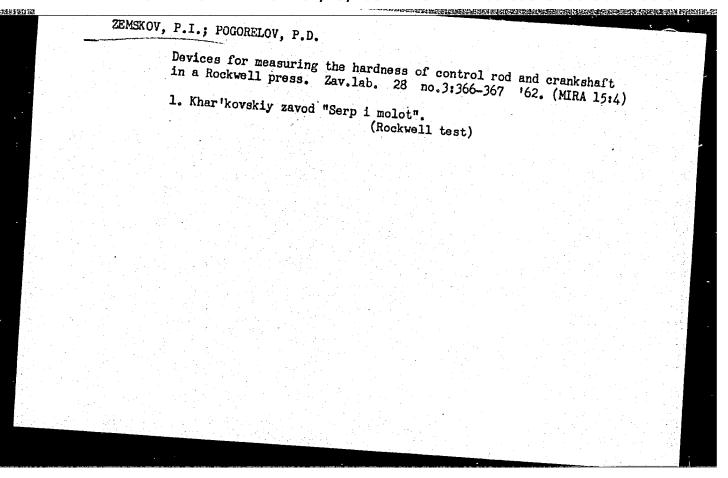
1. Khar'kovskiy institut inzhenerov kommunal'nogo stroitel'stva. (Aluminum alloys--Testing)

Device for testing the hardness of shafts. Mashinostroitel' (MIRA 15:5) (Rockwell test)

(MIRA 17:4)

ZEMSKOV, P.I.; YAKUSHIN, Ye.N.; KHARCHENKO, Ye.N. Wearing resistance of crankshafts from high-strength cast iron. Trakt. i sel'khozmash. no.1:41-43 Ja '64. (MIRA 17:

1. Khar'kovskiy traktornyy zavod.



ZEMSKOV, P.I., kand.tekhn.nauk, dotsent; POCORELOV, I.D., inzh.

Investigating high-grade cast iron as material for piston rings of motor-vehicle engines. Izv.vys.ucheb.zav.; mashinostr. no.4:

(MIRA 15:7)

1. Khar'kovskiy institut kommunal'nogo khozyaystva.

(Cast iron—Testing)

(Piston rings)

ZEMSKOV, P.I., dotsent, kand.tekhn.nauk; POGORELOV, I.D., insh.

Making distributing shafts of gray iron. Izv. vys. ucheb, sav.;
mashinostr. no. 10:106-114 '60. (MIRA 14:1)

1. Khar'kovskiy kommunal'nyy institut.

(Tractors-Engines)

CZEMSKOV, P.I., kand.tekhn.nauk.dotsent; POGORELOV, I.D., inzh.

Comparative data on antifriction properties of some plastics. Izv.vys. ucheb.zav.; mashinostr. no.3177-81 '60. (MIRA 14:3)

1. Khar'kovskiy institut inzhenerov kommunal'nogo stroitel'stva.
(Plastics-Testing)

ZEMSKOV, P.I., dotsent, kand.tekhn.nauk; POGORELOV, I.D., inzh.

Experience in welding and soldering aluminum parts at the "Serp i Molot" Plant in Kharkov. Izv.vys.ucheb.zav.; mashinostr. no.7: 89-95 '59. (MIRA 13:6)

1. Khar'kovskiy institut inzhenerov kommunal'nogo stroitel'stva.
(Electric welding) (Solder and soldering)

ZEMSKOV, P. I. ZEMSKOV, P. I. --"Investigation of the Wear on Piston Rings of Automobile Engines." Min Higher Education Ukrainian SSR. Khar'kov, 1955. (Dissertation for the Degree of Candidate in Technical Sciences.) So.: Knizhnaya Litopis', No. 7, 1956.

ZEMSKOV, P.I., kand.tekhn.nauk, dotsent; POGORELOV, P.D., inzh.

Device for measuring the hardness of a crankshaft. Izv.vys.ucheb.-zav.; mashinostr. no.7:177 '61. (MIRA 14:9)

\$/145/60/000/003/008/010 D221/D301

AUTHORS:

Zemskov. P.I., Candidate of Technical Sciences, Docent and Pogorelov, I.D., Engineer

TITLE:

Comparative data on antifrictional properties of

certain plastics

PERIODICAL:

Izvestiya vysshikh uchbenykh zavedeniy. Mashino-

stroyeniye, no. 3, 1960, 77 - 81

TEXT: The Central Factory Laboratory at the "Serp i molot" plant in Khar'kov investigated antifrictional properties of plastics. Specimen bushes from normal caprone, and also caprone with 3-5 % of an graphite admixture as well as tekstolite, voloknite and fenoplast were tested. The inserts worked with a steel shaft, cr-45 (st-45), R_c - 60 and H_b - 170, and a high strength cast iron, R_c-40, H_c - 170. Browne, babbitt and cast iron bushes were tested for comparison. The purpose was the study of the effect of speed, load, lubricant, material and hardness of shaft on the coefficient of friction. Tests were carried out on an MV (MI) machine. The wear on

Card 1/3

S/145/60/000/003/008/010 D221/D301

Comparative data on antifrictional ...

bushes was measured by analytical balance. The surface of rollers which imitated the shaft was ground. Hardened and untreated rollers were employed. The lubricant was formed by Industrial'noye (Industrial) 20, AK-10 and AH-14 (DP-14) oils and Hepccommaon AW (perssolidol ASh) grease. The minimum wear was exhibited by caprone, especially when having 3 - 5 % graphite additive, $Q = 0.5 \mu$ and Q == 0.1 - 0.2 µ respectively. The war for other plastics was 4 - 5 times greater. This amounted to 2.5 µ for bronge and bebbitt bushes and 10 µ in the case of cast iron insert. The caprone with graphite indicated best antifrictional properties, but the minimum friction torque is shown by babbitt. This torque has a marked tendency to rise at the beginning of running-in of caprone and then falls again The friction coefficient of caprone depends on load and speed, as indicated by graphs. It is highest at low loads. The wear of caprone inserts increases with the hardness of shaft. Cast iron shaft exhibits a smaller friction which is apparently due to greater porosity of former and also on account of lubricating properties of its graphite. The friction in caprone is lower when AK-10 oil is used than when lubricating with "Industrial 20". The minimum friction and wear take place during work of caprone with grease. The Oard 2/3

Comparative data on antifrictional ...

S/145/60/000/003/008/010 D221/D301

authors conclude that caprone is the most suitable for bushes. In the case of inadequate lubrication, caprone with 3 - 5 % of graphite addition is recommended. There are 5 figures.

ASSOCIATION: Khar'kovskiy institut inzhenerov komunal'nogo stroitel

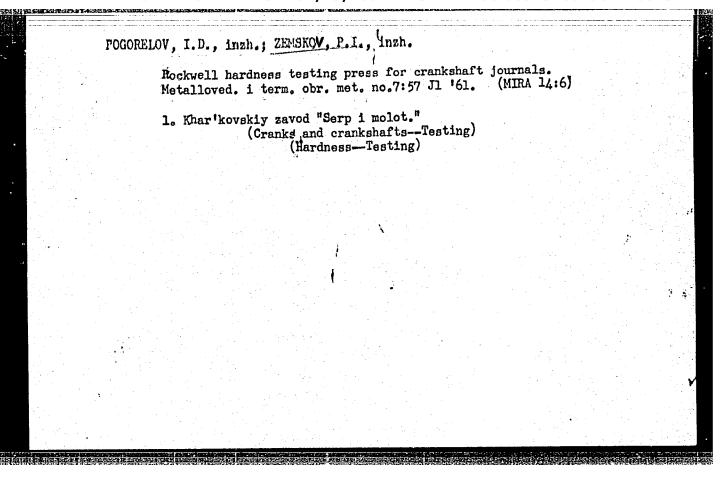
stva (Khar'kov Institute of Engineers of Civil Con-

struction)

SUBMITTED: July 17, 1959

Card 3/3

Investigating the were cast iron in motor—vor 5 162.	ar of piston rings made shicle engines. Avt. pr	of high-strength em. 28 no.9:30-33 (MIRA 15:10)	
1. Kharikovakiy savo	d "Serp i molet".		
(Pist	en rings—Testing)		
경기 교육 기업 전기 기업 등 등에 됩니다. 1987년 - 1987년 - 1987년 1987년 - 1987년			
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AID P - 4288

Subject : USSR/Engineering

Card 1/1 Pub. 128 - 13/25

Authors : Yengalychev, I. M., Engineer and P. I. Zemskov

Title : Experience in sulphide coating at the Khar'kov plant

"Serp i Molot".

Periodical: Vest. mash., #2, p. 46-48, F 1956

Abstract : The sulphide process for surface coating of cast iron

and steel parts to reduce wear and scuffing, particularly between piston rings and cylinders, has been investigated in the Khar'kov plant. Various caustic sulphide baths at different temperatures of treatment are reported. Photos,

tables, chart.

Institution: None

Submitted : No date

ZEMSKOV, P.I., inzh.; YAKUSHINA, Ye.N., inzh.; KHARCHENKO, Ye.N., inzh.; KHAVINA, R.B., inzh.

Engine pinions made from high-strength cast iron. Mashinostroenie (MIRA 18:6)

no.2:12-14 Mr-Ap '65.

ZEMSKOV. P.I., kand.tekhn.nauk; KHAVINA, R.B., inzh.; DEGTYAREVA, O.F., inzh.; YAKUSHINA, Ye.N., inzh.; KHARCHENKO, Ye.N., inzh.; ANISHCHENKO, V.V., inzh.

Capron pinions for motor-vehicle engines. Mashinostroenie (MIRA 18:12)

ZEMSKOV, P.I., dotsent; YAKUSHINA, Ye.N., inzh.; KHARCHENKO, Ye.N., inzh.; KHAVINA, R.B., inzh.; DEGTYAREVA, O.F., inzh.

Cermet piston rings. Izv. vys. ucheb. zav.; mashinostr. no. 10: 123-128 '65 (MIR& 19:1)

1. Submitted April 17, 1964.

LO7438-67 EWT(m)/EMP(t)/ETI IJP(c) JD SOURCE CODE: UR/O145/66/000/004/0059/0063 ACC NR: AP6029220 (A, N) SOURCE CODE: UR/O145/66/000/004/0059/0063 AUTHOR: Zemskov, P. I. (Docent); Yakushina, Ye. N. (Engineer); Knarchenko, Ye. N. (Engineer); C. F. (Engineer); Knarchenko, Ye. N. (
SUB CODE: 13, 13/ SUBM DATE: 18Jun64/ ORIG REF: 002 UDC: 62-47/-242
Aura 2/2

1. TSentral'nyy nauchno-issledovatel'skiy institut bumagi. (Volumetric analysis)	ZEMS/ KAGANSK	Sensitive instrument for conductometric analysis. Jum. prom. 29 no.10: 21-22 0 '54.
		1. TSentral'nyy nauchno-issledovatel'skiy institut bumagi.
가능하는 사용하는 이 교회 전문 보이 가는 것이 되었다. 그는 것은 사람들이 되었다. 그는 것이 되었다. 2015년 대한 제공에 대한 전체의 기업적으로 기업적		

ZEMSKOV, P.

Consolidation of automotive transportation units and centralization of hauling leads to technical development. Avt. transp. 37 no.2:12-15 F '59. (MIRA 13:1)

1. Glavnyy inzhener Glavmosavtotransa.
(Transportation, Automotive)

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AUTHORS:

Sakharova, N.N., Zemskov, S.V.

SOV/ 20-120-3-28/67

TITLE:

Double Chlorides of the Elements of the Cerium Group With Trimethylamine Chloride (O dvoynykh khloridakh elementov tseriyevoy gruppy s khloridom trimetilamina)

PERIODICAL:

Doklady Akademii nauk SSSR, 1958, Vol. 120, Nr 3,

pp. 539-540 (USSR)

ABSTRACT:

Earlier the first author investigated double chlorides (Ref 1) and nitrites (together with G. V. Medoks, Ref 2) of the elements of the group in question with the corresponding tetraphenyl-phosphonium (Refs 3-5). Later Medoks (Ref 6) isolated double nitrates of lanthanum, praseodymium, and neodymium with triphenyl benzyl phosphonium. In continuation of the above mentioned papers the authors included the methylamine-dimethylamine- and trimethylamine chlorides in their investigations. They intended to clear up the nature of the complex formation of the chlorides of rare earths with the corresponding salts of the amides in question in the presence of water and in nonaqueous media according to their degree of substitution. As an introduction it was stated that the chlorides of the 4 metals from several

Card 1/3

Double Chlorides of the Elements of the Cerium Group With Trimethylamine Chloride

SOV/20-120-3-28/67

compounds in the combination with trimethylamine chloride in the presence of 96%-ethyl alcohol, the formation of which is dependent upon the relative amounts of the substances entering interaction, and upon the crystallization conditions. As a result of the conducted work double chlorides of rare earths with trimethylamine in the presence 96%-ethanol were produced. They correspond to the general formuale MeCl₃·4(CH₃)₃N.HCl, where Me denotes La, Ce, Pr and Nd. The properties of these compounds were examined, and the solubility in water and organic solvents was determined. There are 6 references, 6 of which are Soviet.

ASSOCIATION:

Saratovskiy gosudarstvennyy universitet im. N.G. Chernyshevs-kogo (Saratov State University imeni N. G. Chernyshevskiy)

PRESENTED:

January 24, 1958, by I. I. Chernyayev, Member, Academy

of Sciences, USSR

SUBMITTED: Card 2/3

September 10, 1956

Double Chlorides of the Elements of the Cerium SOV/20-120-3-28/67 Group With Trimethylamine Chloride

1. Rare earth chlorides—Chemical reactions 2. Amine chlorides—Chemical reactions 3. Ethanol—Applications 4. Complex compounds—Properties 5. Organic solvents—Performance

Card 3/3

S/137/62/000/001/033/237 A060/A101

AUTHORS:

Koz min, Yu. A., Zemskov, S. V., Ryabinin, A. I.

TITLE:

Application of the sulfide-sulfite method in the processing of

tellurium-containing materials

PERIODICAL:

Referativnyy zhurnal, Metallurgiya, no. 1, 1962, 22, abstract 10164 ("Metallurg: 1 khim. prom-st' Kazakhstana. Nauchno-tekhn. sb.",

1961, no. 1(11), 23-25)

TEXT: The authors studied the possibility of applying the sulfide-sulfite method to the processing of rich Te-containing products. It is shown that this method ensures the extraction of 93 - 94% of the Te from the primary hydroxide (at an Na₂S expenditure of 5 - 6 kg per 1 kg Te) as against 60 - 70% extraction by the soda method, and when soda slags are processed - 81-84% versus 40-50%. The reagent expenditure and process duration are reduced when the sulfide-sulfite method is used.

G. Svodtseva

[Abstracter's note: Complete translation]

Card 1/1

Oxidation of cis- and trans-isomers of bivalent platinum by sodium vanadate. Zhur. neorg. khim. 10 no.6:1502-1503 Je 165. (MIRA 18:6)

1. Institut neorganicheskoy khimii Sibirskogo otdeleniya AN SSSR.

ZEMSKOV, S.V.; PTITSYN, B.V.

Oxidation of the platinite series by sodium vanadate. Dokl. AN SSSR 160 no.2:343-345 Ja '65.

1. Institut neorganicheskoy khimii Sibirskogo otdeleniya AN SSSR.

2. Chlen-korrespondent AN SSSR (for Ptitsyn).

SAKHAROVA, N.H.; ZEMSKOV, S.V.

Double chlorides of cerium group elements and trimethylemine chloride. Dokl. AN SSSR 120 no. 3:539-540 My '58. (MIRA 11:7)

1. Saratovskiy gosudarstvennyy universitet im. N.G. Chernyshevskogo.
Predstavleno skademikom I.I. Chernysyevym.
. (Rare earth chlorides)
(Trimethylamine)

8/137/62/000/001/032/237 A060/A101

AUTHORS:

Koz'min, Yu. A., Ryabinin, A. I., Zemskov, S. V.

TITLE:

On the oxidation of tellurium up to the tetravalent state

PERIODICAL:

Referativnyy zhurnal, Metallurgiya, no. 1, 1962, 22, abstract 10163 ("Metallurg. 1 khim. prom-st' Kazakhstana. Nauchn.-tekhn. sb.", 1961, no. 2(12), 57-61)

TEXT: A study was made as to the possibility of obtaining water-soluble Te from anodic copper electrolytic slimes by producing a definite composition of the gaseous phase and the charge preparation schedule. It was established that in the course of oxidizing roasting of the slime with soda the Te is transformed almost entirely into the hexa-valent variety, and in the course of the aqueous lixiviation of the clinker if remains in the cake. Calcination of the clinker in a stream of CO₂ or N₂ at 700 - 750°C affords the possibility of transforming 70% and more of the Te into the tetra-valent, soluble variety. The reduction of Te to Te by carbon monoxide occurs at lower temperatures. In the laboratory investigations the transformation of Te into Te constituted 80 - 90%.

[Abstracter's note: Complete translation]
Card 1/1

NIVOSELOV, R.I.; ZEMSKOV, S.V.; PTITSYN, B.V.

Oxidation of tetrammine platinum chloride by iodine. Dokl. AN SSSR 158 no.5:1133-1135 0 64. (MIRA 17:10)

1. Institut neorganicheskoy khimi cibirskogo otdeleniya AN SSSR. 2. Chlen-korrespondent AN SSSR (for Ptitsyn).

CHERNYAYEV, I.I.; ZEMSKOV, S.V.; PTITSYN, B.V. [deceased]

Oxidation-reduction properties of nitrite complexes of platinum. Zhur.neorg.khim. 10 no.11:2404-2410 N 165.

1. Institut neorganicheskoy khimii Sibirskogo otdeleniya AN SSSR. Submitted May 5, 1964.

ZEMSKOV, V.A. (Leningrad); MAKAR'YEV, B.M. (Leningrad)

Improvement of the characteristics of automatic control systems of a certain class using nonlinear control signs. Izv. AN SSSR.

Tekh. kib. no.6:60.71 N-D '63. (MIRA 17:4)

ZEMSKOV, V.A. (Leningrad); MAKAR'YEV, B.M. (Leningrad) Improvement of the interference rejection of a class of automatic control systems by means of nonlinear control laws. Izv.

AN SSSR. Tekh. kib. no.1:143-149 Ja-F '65.

。 1984年 - 1985年 - 19

(MIRA 18:4)

GONCHAREVICH, Igor' Fomich; EMSKOV, Vasiliy Dmitriyevich; KORESHKOV,
Viktor Ivenovich; BRILLIANTOV, V.V., otv.red.; GARECR, P.M.,
red.izd-va; BOLDTREVA, Z.A., tekhn.red.

[Shaker screens and conveyers] Vibrataionnye grokhoty i
konveiery. Moskva, Gos.nauchno-tekhn.izd-vo lit-ry po gornomu
delu, 1960. 214 p. (MIRA 14:3)

(Screens (Mining)) (Conveying machinery)

ANDREYEV, S. Ye.; BOKIY, B. V.; GORODETSKIY, P. I.; OREYVER, N. S.; SHCHUKIN, A. A.

GERONT! YEV, V. I.; SECCHDISKIY, A. A.; TERPIGOREV, A. M.; SHEVYAKOV, L. D.;

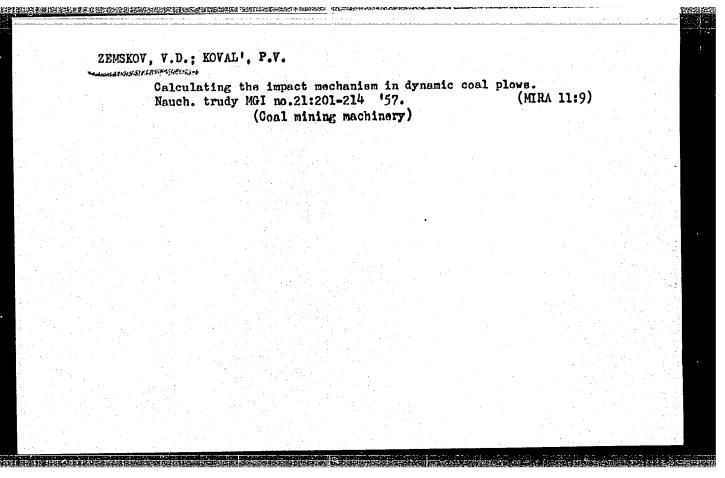
SPIVAKOVSKIY, A. A.; VERRHOVSKIY, I. M.; VORGIKOV, I. M.; YELANGHIK, G. M.;

KASHIN, N. V.; SLOBODKIN, M. I.; GUZENKOV, P. G.; ZEMSKOV, V. D.; HOVIKOV, F. S.

OSETSKIY, V. M.; SOSUMOV, G. I.; YASYUKEVICH, S. M.; KHAY, G. A.; POPOV, V. M.

In memory of Professor Levenson. Gor. zhur. no. 9:60 S '55.

(Levenson, Lev Borisovich, 1878-1955)



ZEMSKOV, V.D., kandidat tekhnicheskikh nauk; BRILLIANTOV, V.V., kandidat tekhnicheskikh nauk; VINOGRADOV, N.N., kandidat tekhnicheskikh nauk.

A misconception constantly appearing in books on ore dressing.

Ugol 32 no.4:47-48 Ap 57. (MERA 10:5)

Moskovskiy gornyy institut.
 (Ore dressing)

· ZEMSKOV V. D.

127-58-1-15/28

AUTHORS:

Verkhovskiy, I.M., Professor, Doctor of Technical Sciences; Zemskov, V.D., and Vinogradov, N.N., Candidates of Technic-

al Sciences; Arutinov, O.M., Engineer-Physicist

TITLE:

Investigation by the Gamma-Location Method of Some Regularities in the Jigging Process (Issledovaniye nekotorykh zakonomernostey protsessa otsadki metodom gamma-lokatsii)

PERIODICAL:

Gornyy Zhurnal, 1958, Nr 1, pp 53-56 (USSR)

ABSTRACT:

Numerous versions of the "marked atoms" method employed at present do not make possible the study of the kinetics of the spatial motion of grains in media with different absorption coefficients. Therefore, the Chair of Concentration at the Moscow Mining Institute developed a new method, named "gamma-location", for the continuous study of mineral grain motion. The gamma-location method makes it possible to record continuously the spatial displacements of a particle under investigation into which a radioactive isotope with hard gamma-radiation is inserted. The block-diagram of the equipment is shown in Figure 1. The equipment consists of the following basic parts: 1) an indicator

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127-58-1-15/28

Investigation by the Gamma-Location Method of Some Regularities in the Jigging Process

system; 2) an electronic computer; 3) an oscillograph; 4) a high-voltage stabilized amplifier, and 5) a stabilizer of voltage. The essence of the gamma-location method consists in that the spatial motion of the grains is brokendown into 3 coordinates, by means of special systems of indicators. The motion of the grain along each coordinate is continuously recorded as a function of time. The indicator systems consist of standard discharge counters situated according to a definite system, called "carpets". The electronic computer converts the pulses into direct current proportional to their frequency. It consists of several similar channels corresponding to the number of coordinates being measured simultaneously. The results permit the discovery of basic laws of grain motion in jigging machines. For instance, the graph of the motion of a heavy grain represents a monotonous function (shown in Figure 2) which indicates that the grain continuously sinks to the bottom layer. The motion of light grains has a "jump-like" character shown in Figure 3. Analysis of the results shows that the state of intermediate, slightly loosened layers

Card 2/3

127-58-1-15/28

Investigation by the Gamma-Location Method of Some Regularities in the Jigging Process

(thickness and degree of loosening) is a criterion of the jigging process which determines the specific weight of separation and the quality of concentration products. The intermediate layers serve as a filter which passes down only grains of a definite specific gravity. The filtering properties of the intermediate layer depend upon many factors: specific gravity and size of the grains, the magnitude of hydrodynamic forces, and mechanical interaction forces between the grains. The establishment of the effects of these factors calls for extensive investigations. The article contains 1 figure, 2 graphs, and 7 references, of which 5 are Soviet and 2 English.

ASSOCIATION: Moskovskiy gornyy institut (Moscov Mining Institute)

AVAILABLE: Library of Congress

Card 3/3 1. Tracers-Applications 2. Isotopes (Radioactive)-Applications

3. Gamma rays-Applications 4. Mining engineering-USSR

Basic problems in the theory of unbalanced shaker screen performance, Nauch, dokl. vys. shkoly; gor. delo no.2:281-296 '58.

(MIRA 11:6)

1. Predstavlena kafedroy obogashcheniya polesnykh iskopayemykh Moskovskogo gornogo instituta im. I.V. Stalina.

(Screens (Mining))

ZEMSKOV, V.D., dots., kand.tekhn.nauk

Analysis of transition processes in vibrating screens. Nauch.dokl. vys.shkoly; gor.delo. no.4:231-240 '58. (MIRA 12:1)

1. Predstavleno kafedroy obogashcheniya poleznykh iskopayemykh Moskovskogo gornogo instituta imeni I.V. Stalina. (Screens (Mining))

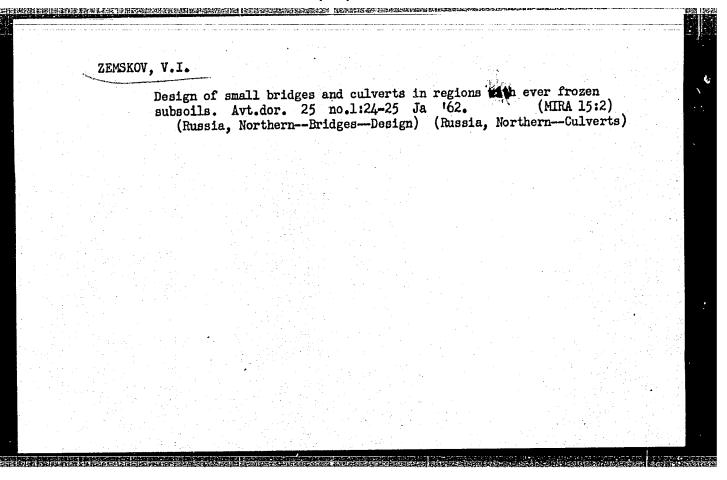
ZEMSKOV, V.D.: BRILLIANTOV, V.V.; VINOGRADOV, N.N.; SHOKHIN, V.N.

Electric measurement methods in investigating wet gravity ore dressing processes. Nauch. trudy MGI no. 32:5-14 '60.

(Ore dressing) (Electric measurements)

ZHGULEV, Al'bert Sergeyevich; ZEMSKOV, V.D., kand. tekhn. nauk, retsenzent; HRILLIANTOV, V.V., kand. tekhn. nauk, otv. red.; GARBER, T.N., red.izd-va; LAVRENT'YEVA, L.G., tekhn. red.

[Electrovibrating machine operator] Mashinist elektrovibrationnoi mashiny. Moskva, Gosgortekhizdat, 1963. 91 p. (MIRA 16:12) (Ore dressing--Equipment and supplies) (Vibrators)



ZENSKOV, V.M., prof.

C-reactive protein in the diagnosis of some cardiovascular diseases (coronary insufficiency, rheumatism). Vrach. delo no.6;22-26 Je '61. (MIRA 15;1)

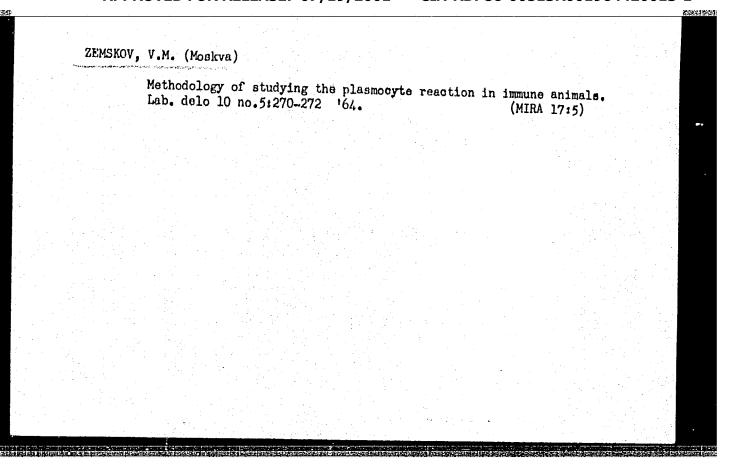
1. Kafedra fakul'tetskoy terapii (zaveduyushchiy - M.N.Tumanovskiy) i kafedra mikrobiologii (zaveduyushchiy - prof. M.V.Zemskov)

Voronezhskogo meditsinskogo instituta.

(BLOOD PHOTEINS) (HEART FAILURE)

(RHEUMATIC FEVER)

ZEMSKO	V, V.M.			
	Dynamics of C-reactive protein and leucocytes in myocardial i	n, erythrocyte sedimer infarct. Lab. delo 7	ntation reaction, no.3:20-22 (MIRA 14:3)	
	l. Kafedra fakul'tetskoy terap i Kafedra mikrobiologii (zav. meditsinskogo instituta. (BLOOD PROTEINS) (LEUCOCYTES)	pli (zav prof. M.N prof. M.V.Zemskov) (ERYTHROCYTES) (HEART-INFARCTION	Voronezhskogo	



PETROV, R.V.; ZEMSKOV, V.M.; PASHININ, P.M.

Place of the formation of S-reactive protein in radiation injury. Radiobiologiia 5 no.4:511-513 '65. (MIRA 18:9)

ZEMSKOV, Vladimir Mikhaylovich; SOROKO, Ya.I., red.

[Weapons of invisible enemies] Oruzhie nevidimykh vragov.
Moskva, Izd-vo "Znanie," 1964. 39 p. (Novoe v zhizni,
nauke, tekhnike. VIII Seriia: Biologiia i meditsina, no.11)
(NIRA 17:7)

ZEMSKOV, V.M.

Morphological indices of immunity; a review. Zhur. mikrobiol., epid. i imm. 41 no. 2:25-28 F '64. (MIRA 17:9)

137-58-6-12122

Translation from: Referativnyy zhurnal, Metallurgiya, 1958, Nr 6, p 134 (USSR)

AUTHORS: Petrov, D.A., Kekua, M.G., Dashevskiy, M.Ya., Zemskov,

V.S., Petrusevich, R.L.

TITLE: Progress of Work on the Refining of Germanium by Means of Crystallization and Achievement of Germanium Single Crystals

With Longitudinally Homogeneous Properties (Razvitiye rabot po ochistke germaniya metodami kristallizatsii i polucheniye monokristallov germaniya s ravnomernymi svoystvami po

dline)

PERIODICAL: V sb.: Vopr. metallurgii i fiz. poluprovodnikov. Moscow,

AN SSSR, 1957, pp 50-58

ABSTRACT: Experiments were performed in order to investigate the

possibilities of producing single crystals with uniform longitudinal and cross-sectional distribution of impurities by means of pulling at a controlled rate as well as by pulling accompanied by constant feeding of pure Ge into the melt. The raw polycrystalline material with a ρ of 5-20 ohm/cm was purified by means of zonal recrystallization under a vacuum of 10^{-4} mm

Hg, or in a stream of H2, until it exhibited a φ of 50-60

Card 1/3 ohm/cm. A high-frequency heating apparatus with three

137-58-6-12122

Progress of Work on the Refining of Germanium (cont.)

induction units moving back and forth was employed. It was found that single Ge crystals, grown by the Chokhralskiy method from purified material with a ρ of 50-60 ohm/cm in conjunction with mixing of the melt by rotating the crucible and the growing crystal, can achieve ρ and τ values of 60 ohm/cm and 1000 μ sec, respectively; if the rotation is omitted from the growth process, the o and the T amount to 25-50 ohm/cm and 200-250 µ sec, respectively. The UVM-2 apparatus, employed in the process of pulling the crystal under vacuum (10-4 mm Hg) in accordance with scheduled variations of the rate of pulling, utilizes a hydraulic raising mechanism which provides a smooth variation of the elevation rate from 0.05 to 8 mm/min in conjunction with the rotation of the crucible and the growing crystal. The Q value of grown crystals 50 mm in diameter and 180 mm long deviated from the mean value of ~ 40 -60 ohm/cm, at a length of 100-150 mm, by 8.9-9.3% and was within the limits of error of measurement. It is pointed out that because of variations in conditions of crystallization only macrouniformity in the distribution of impurities can be achieved by this method. The variations were eliminated in another device which was designed for a process in which the pulling is accompanied by feeding of pure Ge into the melt. Prior to immersion into the melt, the feed ingot passes through a heating unit (composed of a quartz tube wound with W wire), while the ingot being pulled passes Card 2/3

137-58-6-12122

Progress of Work on the Refining of Germanium (cont.)

through a water-cooled unit made of stainless steel. The process of pulling was carried out in an Ar atmosphere. The fact that the feed ingot and the growing crystal, which may rotate, were placed excentrically with respect to the axis of rotation of the crucible, contributed to a better mixing of the melt contained in the crucible. It was found that the longitudinal Q fluctuations in single crystals obtained by this method did not exceed ±5%, whereas in the case of a crystal produced in this apparatus without the employment of pure Ge the scatter amounted to ± 24%. Studies of crystals with a diameter of 50 mm have revealed that the ho was sufficiently uniform throughout the cross section of the crystal and that the diffusion-path length of minority current carriers did not deviate by more than 10-15%. The authors express the opinion that intensive cooling of the growing crystal, which results in the achievement of a plane crystallization front, contributes to uniform distribution of electrical properties throughout the cross section of the crystal. Grown single crystals which exhibited nonuniform crosssectional distribution of ρ were subjected to heat treatment in order to bring about a redistribution of ρ values; in the process the mean value of resistivity remained unaltered, while the diffusion-path length of the minority current carriers increased somewhat. 1. Germanium--Processing zation 3. Single crystals--Growth 4. Single crystals--Processing 2. Germanium--Crystalli-4. Single crystals--Properties Card 3/3

ZEMSKOV, V.S.

137-58-5-9454

Translation from: Referativnyy zhurnal, Metallurgiya, 1958, Nr 5, p 92 (USSR)

Petrov, D.A., Zemskov, V.S. AUTHORS:

Equipment and Methods of Growing Single Crystals of Semi-TITLE:

conductors (Apparatura i metody vyrashchivaniya mono-

kristallov poluprovodnikov)

V sb.: Rost kristallov. Moscow, AN SSSR, 1957, pp 262-PERIODICAL:

272

An examination is made of the equipment and the results obtained in growing single crystals of Ge by the Chokhral'skiy ABSTRACT:

'method and by drawing with feeding of additional substance. Drawing was performed by means of an apparatus consisting of 3 parts. At the bottom there was mounted a vacuum circulation chamber, connected with a system for evacuation. Water-cooled electrodes, to which were mounted a graphite slit heater and screens, were introduced into the chamber. Into the chamber from beneath there was introduced a motor-rotated rod carrying a crucible base. A quartz beaker with a viewing tap was placed

atop the circulation chamber on rubber gaskets. The beaker was closed at the top by a water-cooled cover, to which was mounted Card 1/2

137-58-5-9454

Equipment and Methods of Growing Single Crystals of Semiconductors

a mechanism for raising and rotating the seed-crystal-carrying finger passing through the cover into the chamber. The apparatus provided a vacuum of $\sim 10^{-4}$ mm Hg. The cover and lower chamber were connected by bolts for operation in a gas atmosphere. It is noted that in order for a single crystal to be grown the temperature of the melt should increase from its center toward the bottom and the walls of the crucible; some degree of overheating of the melt tends to increase the reliability of single crystal formation. To produce a single crystal, the seed crystal has to be fused along the entire interface between seed crystal and melt. Rotation of the crucible and the growing crystal is conducive to symmetrical growth of the crystal, but when the rate of crystal rotation is N350 rpm, formation of a screw-shaped crystal is observed. There is a brief examination of the distribution of impurities in the drawing process. Changes in the apparatus to permit feeding of additional substance are described. The crystal being fed is passed through the heater, while the crystal being drawn passes through a cooler. This apparatus made it possible to obtain uniform longitudinal distribution of In 114 along the single crystal drawn when a melt of pure Ge was fed in. This was verified by autoradiograph photometry and by resistance measurement (resistance variations of $\pm 5\%$). The importance of good mixing of the melt on drawing with feeding of additional substance is noted. 1. Single crystals--Growth 2. Germanium crystals--Growth Card 2/2 3. Indium isotopes (Radioactive) -- Applications 4. Autoradiography -- Applications

5. Semiconductors--Crystal structure

CHERKASHIN, Yevgeniy Yevgeniyevich; GLADYSHEVSKIY, Ye.I., dotsent, otv.
red.; ZEMSKOV, V.S., red.; SARANYUK, T.V., tekhred.

[Metric analysis of chemical equilibrium diagrams of systems containing associated components] Metrika ravnovesnoi khimicheskoi diagrammy sistem s assotsiirovannymi komponentami.
Izd-vo L'vovskogo univ., 1958. 106 p. (MIRA 11:12)

(Systems (Chemistry))

LENEVICH, Lev Grigor'yevich, prof.; ZEMSKOV, V.S., red.; MALYAVKO,

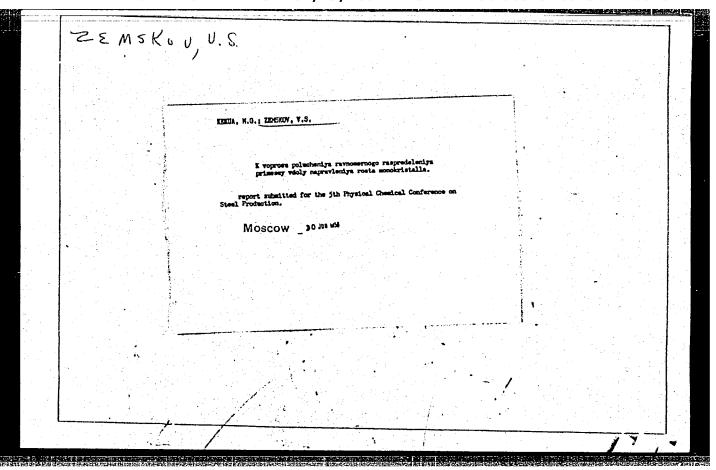
A.V., tekhred.

[Multiview method in descriptive geometry] Bezosnyi metod
v nachertatel'noi geometrii. Izd-vo L'vovskogo univ., 1958.

155 p.

(Geometry, Descriptive)

(MIRA 12:4)



3-34 67293 24.7700 sov/180-59-4-26/48 V.S., Petrov, D.A. and **AUTHORS:** Zhurkin, B.G., Zemskov, Suchkova, A.D. (Moscow) The Nature of the Quasi-Binary Germanium-Indium-Antimony TITLE: System PERIODICAL: Izvestiya Akademii nauk SSSR, Otdeleniye tekhnicheskikh nauk, Metallurgiya i toplivo, 1959, Nr 4, pp 156-158 (USSR) Germanium with electron-type conduction and a specific ABSTRACT: resistance 25 to 30 ohm/cm was used together with zone refined antimony and indium. Crystals were pulled from the melt. Results are given in Table 1. All the samples had electron-type conductivity and samples with high InSb content had a higher concentration of electrons than those with low InSb content. The number of current carriers varied from 1.2×10^{18} to 1.9×10^{19} /cm³. The value for fully compensated additions is $2.5 \times 10^{13}/\text{cm}^3$. Thus there was an excess of Sb atoms. Experiments were carried out using the same Ge:Sb ratio and increasing the In content. Results are given in Table 2. With a ratio of In: Sb of 2.5 there is still electronic conduction very near to the compensated alloy. With In:Sb = 4.4 there is hole-type Card 1/2 conduction. Microstructures were examined along the

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SOV/180-59-4-26/48
The Nature of the Quasi-Binary Germanium-Indium-Antimony System

length of the crystal pulled from a melt. A second phase appears (see Fig) which from microhardness tests corresponds to InSb. It does not appear, however, at temperatures greater than 650°C - the temperature of dissociation of InSb. The authors conclude that because of dissociation of InSb in fused germanium, the system does not possess the properties of a quasi-binary system. There are 1 figure, 2 tables and 8 references, 6 of which are Soviet and 2 English.

SUBMITTED: March 16, 1959

Card 2/2

67801 24.7600 SOV/180-59-5-13/37 AUTHORS: Zhurkin, B.G., Zemskov, V.S., Petrov, D.A., and Suchkova, A.D. (Moscow) The Solubility of Indium and Antimony in Germanium and TITLE: their Effect on some Electrical Properties of Germanium PERIODICAL: Izvestiya Akademii nauk SSSR, Otdeleniye tekhnicheskikh nauk, Metallurgiya i toplivo, 1959, Nr 5, pp 86-90 (USSR) ABSTRACT: Single crystals of germanium were pulled from melts doped with up to 80 wt % of indium or of antimony. [111] seeds were used; growth rate was 0.04 mm/min and the crystal was rotated at 140 rpm. Starting materials were: high purity germanium (25-30 ohm.cm N-type, mobility 3600 cm²/V.sec, diffusion length $\sim 1.5-2$ mm); indium showing spectrographic traces of Fe, Al, Cu, Ca, Ni and A pure graphite antimony of Gu, As, Pb, Au, Al and P. crucible fitted with a quartz sheathed thermocouple (Fig 1) held a charge of 10-12 g. The pulled ingots were 7-9 mm diameter and 8-10 mm long. These were cut in half lengthways. One half was studied metallographically for homogeneity while Hall effect specimens (7 x 3 x 1 mm) Card Were cut from the other, close to the seed and 1/3 perpendicular to the growth axis. Resistivity and Hall

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SOV/180-59-5-13/37

The Solubility of Indium and Antimony in Germanium and their Effect on some Electrical Properties of Germanium

emf were measured with a potentiometer type PPTN-1 and a galvanometer type M-25/3. Resistivity measurements were ± 5% but Hall measurements (3700 0e field) for the higher impurity concentrations had greater errors, from 10-50%。 In determining impurity concentrations from resistivity and Hall measurements complete ionization and degeneracy were assumed. The table shows equilibrium concentrations of indium and antimony in solid and liquid germanium at various temperatures (both wt % and at % values are given). The corresponding phase diagrams are plotted in Figs 3 and 4 (compositions in at %). Solid Ge containing 6.6.10-2 at % In is in equilibrium with a melt containing 71.6 at % In at 620 °C, and solid germanium containing 7.2 . 10-2 at %Sb with liquid containing 70.5 at % Sb at 693 °C. Extrapolation to the eutectic horizontals suggests maximum solid solubilities of 8 . 10-2 at % In and about 0.1 at % Sb. No retrograde solid solubility was found for Sb. Fig 5 shows log-log plots (which are linear)

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The Solubility of Indium and Antimony in Germanium and their Effect on some Electrical Properties of Germanium

of resistivity vs impurity concentration for Sb (1) and In (2) doping. 2.5 x 10-19 Sb/cm3 gave ~6.16-4 ohm.cm, and 2.10-19 In/cm3 gave 2.10-3 ohm.cm. Fig 6 shows the corresponding variations in Hall mobility; the plots for both holes and electrons varying similarly. The results presented for In are in good agreement with those in Ref 3. There are 6 figures, 1 table and 14 references, of which 3 are Soviet, 10 English and 1 German.

SUBMITTED: April 3, 1959

Card 3/3

S/180/61/000/006/018/020 E073/E535

AUTHORS: Zemskov, V.S., Suchkova, A.D. and Wang Kuei-Hua

(Moscow)

TITLE? On the nature of beterogeneous equilibrium in the

system germanium-aluminium-antimony

PERIODICAL: Akademiya nauk SSSR. Izvestiya. Otdeleniye tekhnicheskikh nauk. Metallurgiya i toplivo. no.6, 1961, 149-151

TEXT: In earlier work of the authors and their team (Ref.1: Izv.AN SSSR, OTN, Metallurgiya i toplivo, 1959, No.4) it was established that the Ge-fnSb in the ternary Ge-In-Sb does not represent the real equilibrium between the solid and liquid phases during crystallization and, consequently, does not have all the properties of a binary system. Therefore, the necessity arose to verify the results obtained with the Ge-In-Sb system on other systems and the Ge-Al-Sb system was chosen for this purpose. The AlSb compounds are thermally more stable than InSb compounds and, therefore, it was to be anticipated that the behaviour of aluminium and antimony during crystallization of Card 148 4

On the nature of heterogeneous ... \$/180/61/000/006/018/020 E073/E535

germanium will differ from the behaviour of In and Sb. investigating this system, the method of drawing the primary crystals of the solid solution from the appropriate melts containing various quantities of the alloying components was chosen. Measures were taken for creating equilibrium conditions of crystallization and for obtaining single-crystal specimens. The specimens were drawn at a rate of 0.045 mm/min; the seed was rotated at a speed of 100 to 120 r.p.m. and the crucible remained The germanium used had a specific resistance of stationary. 14 Ohmer and a diffusion length of 2.5 mm and an aluminium impurity content not exceeding 10^{-4} %; the autimous was grade CY -000 (SU-000). On the drawn crystals of the solid solutions the Hall constant and the specific resistance were measured. Two sections of the system containing 98 and 97 at. % Ge with various ratios of Al and Sb contents were investigated. The compositions of the initial melts of germanium from which primary crystals were produced are those given in Table 1, On the basis of the measured values of the Hall constant, the specific resistance of the solid solution crystals, of the determination Card 2/# 4

On the nature of heterogeneous ... S/180/61/000/006/018/020 E073/E535

of the type of conductivity and of the calculated values of the concentrations of the current carriers, graphs were plotted of the changes in the electric parameters of the solid solutions as a function of the concentrations of Al and Sb in the conjugate liquid phases. It can be seen that crystals drawn from melts with an equi-atomic ratio of Al and Sb contents (curves a and b,) have a clearly pronounced hole-type conductivity. A change in the ratio of these elements until the Sb atoms predominate above the Al atoms by a factor of 20 does not lead to a change in If the ratio equals 22 to 25, the the type of conductivity. crystals will have a mixed-type conductivity and only if the content of Sb is over 25 times that of the Al content will there An increase in the he a change to electron conductivity. content of Sb in the liquid phase as compared to the content of Al leads to a change in the ratio of these elements in the solid phase towards full compensation, thereby reducing the number of current carriers, and the specific resistance will begin to increase. After compensation, the type of conductivity changes into electron conductivity and the specific resistance will again Card 3/6

On the nature of heterogeneous ... S/180/61/000/006/018/020 E073/E535

drop as a result of an increase in the quantity of Sb atoms above that of the Al atoms. In the system Ge-Al-Sb the observed changes in the electric characteristics are similar to those occurring in the system Ge-In-Sb; the section Ge-AlSb in the system Ge-Al-Sb is also not quasi-binary. If the ratio of the Sb atoms to the In atoms in the melt is 22 to 25, i.e. approaching the ratio of the coefficients of distribution of Al and Sb in binary systems with germanium (for Sb the coefficient of distribution at the given temperature is 2.9 x 10^{-3} and for Al it is 7×10^{-2}), the solid phase crystallizes with an equinatomic ratio of Al and Sb atoms. The observed behaviour can be explained by dissociation of antimonides in the melting. There are 2 tables, I figure and 3 Soviet-bloc references.

SUBMITTED: May 18, 1961

Card 4/69 4

24,7700 (1035,1043,1055)

0793 S/181/61/003/011/038/056 H104/B102

AUTHORS:

Zhurkin, B. G., Zemskov, V. S., and Yurkina, K. V.

TITLE:

Hall mobility of electrons in highly alloyed n-type

germanium

PERIODICAL:

Fizika tverdogo tela, v. 3, no. 11, 1961, 3509 - 3513

TEXT: The Hall mobility of electrons in n-type germanium monocrystals alloyed with antimony (up to 2.5·10¹⁹ cm⁻³) and arsenic (up to 6.0·10¹⁹ cm⁻³) was studied. Specimens cut frommonocrystal inguts were used for measurements carried out at room temperature. The specimens had the dimensions 7·3·1 mm, the ingots had been produced by crystal pulling. The method of manufacturing strongly alloyed germanium was described in previous papers (B. G. Zhurkin et al., Izv. AN SSSR, OTN, no. 5, p. 86, 1959; V. S. Zemskov et al., Tezisy dokl. na konf. po udarnoy ionizatsii i tunnel nomu effektu v poluprovodnikakh, Baku, 14 - 17, 1960). Electron-electron collisions were not taken into account because of degeneration in alloyed germanium. The Hall mobility was computed by the relation Card 1/3

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Hall mobility of electrons in highly ...

μ = R/q, where R is the Hall constant and q the resistivity. The two latter quantities were measured with the use of a filth (PPTN-1) voltmeter and an M25/3 (M25/3) galvanometer by a d-c compensation method. Magnetic fields of 3800-4200 oe were employed to measure R. The measuring error of q was ± 5 %, that of the Hall-emf ± (10-20)%. The results showed that the Hall mobility of the electrons in germanium alloyed with antimony (10¹⁸ - 10¹⁹ cm⁻³) by far exceeds that of germanium of equal arsenic concentration. At an impurity concentration of about 10¹⁹ cm⁻³ the Hall mobility of electrons in germanium alloyed with antimony is almost twice that in germanium alloyed with arsenic. It is assumed that this difference is due to a change in effective electron mass m, with the impurity. When electron scattering from impurity atoms and lattice vibrations was taken into account, an estimation of the effective masses mn(Sb) and mn(As) showed that within the concentration range of 5.10¹⁷ - 2.5·10¹⁹ cm⁻³ m(Sb) was changed from 0.19 m to 0.30 m. In the range of arsenic concentration

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Hall mobility of electrons in highly...

of 5.10¹⁷ - 5.10¹⁹ cm⁻³, m_n(As) was changed from 0.195 m to 0.52 m. The authors thank B. M. Vul', L. V. Keldysh, and V. A. Chuyenkov for discussions. There are 1 figure, 2 tables, and 10 references: 3 Soviet and 7 non-Soviet. The three most recent references to English-language publications read as follows: W. Waring, D. Pitman, S. Steele, J. Appl. Phys., 29, no. 6, 1002, 1958; W. E. Baker, D. M. Compton. J. B. M. J. Res. and Develop., 4, no. 3, 275, 1960; M. Cardona, W. Paul, H. Brooks. Helv. phys. acta, 33, no. 5, p. 329, 1960.

ASSOCIATION:

Institut metallurgii im. A. A. Baykova AN SSSR Moskva (Institute of Metallurgy imeni A. A. Baykov AS USSR, Moscow)

SUBMITTED:

March 3, 1961 (initially) July 3, 1961 (after revision)

Card 3/3

Precarious period of a war and vigilance. S '61.		ilance. Voen. ve	est. 41 no.	41 no.9:31-33	
	, 1914-1918) (Wor (United StatesM	rld War, 1939-194 Militarism)	(MIRA 1 +5)	5:1)	
			*.		

\$/058/63/000/002/045/070 A062/A101

AUTHOR:

Zemskov, V. S., Zhurkin, B. G., Suchkova, A. D., Yurkina, K. V.

TITLE:

Production and properties of strongly alloyed germanium

PERIODICAL: Referativnyy zhurnal, Fizika, no. 2, 1963, 71, abstract 2E473 ("Tr. Soveshchaniya po udarn, ionizatsii i tunnel'n, effektu v poluprovodnikakh, 1960". Baku, AN AzerbSSR, 1962, 130 - 150)

By the method of extracting the solid phase from a smelt with a large content of alloying admixture, single crystals of Ge were obtained with a concentration of Al up to $1.0 \cdot 10^{21}$ cm⁻³, with a concentration of As up to $6.0 \cdot 10^{19}$ cm⁻³, with a concentration of Sb up to $2.5 \cdot 10^{19}$ cm⁻³ and with a concentration in In up to 2.0.1019 cm-3. It is established that there is an increase of solubility of In and Sb in Ge at a combined alloying, and this is explained on the basis of the electron-hole interaction in the solid phase. Applying the method of quantitative radiography and measuring the Hall effect made it possible to determine separately the concentration of In and Sb in the solid phase of Ge, while the data on the Hall mobility show an absence of neutral ion pairs [In-Sb+]o. It was found that

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Production and properties of ...

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at room temperature the Hall mobility in Ge with Sb, in the range of Sb concentrations from $2 \cdot 10^{10}$ to $5 \cdot 10^{19}$, is about twice as high as the Hall mobility in Ge with As at equal concentrations of the admixtures.

[Abstracter's note: Complete translation]

Card 2/2

37735

S/180/62/000/002/014/018 E039/E435

19. 8100 AUTHORS:

Zemskov, V.S., Suchkova, A.D., Zhurkin, B.G.,

Wang Kuei-Hua (Moscow)

TITLE:

The solubility of aluminium in germanium and the

influence of aluminium on some electrical properties of

germanium

PERIODICAL: Akademiya nauk SSSR. Izvestiya. Otdeleniye tekhnicheskiki nauk. Metallurgiya i toplivo. no.2, 1962, 131-134

TEXT: The initial materials used were electron type germanium with a specific resistance of 50 ohm cm and aluminium purified by zone melting containing Fe \langle 7 x 10⁻⁴%, Mg 2 x 10⁻⁴%, Si 4 x 10⁻⁴%, Cu 5 x 10⁻⁵% and Zn \langle 1 x 10⁻⁴%. Alloys were prepared by the extraction method and all the investigated samples were single phase. The region of solid solution was investigated at 675°C. It is shown that the concentration of Al in solid solution varied from 9.97 x 10⁻³ at.% at a concentration of Al of 0.1 at.%, to 1.544 at.% at \langle 46.2 at.% Al. A solidus curve is plotted on which is included results from earlier papers. Good agreement is obtained at .850°C but the earlier results Card 1/2

S/180/62/000/002/014/018 E039/E435

The solubility of aluminium ...

give rather lower values of Al concentration at temperatures less The concentration of current carriers was determined by measuring the Hall constant in a magnetic field of 4000 oersted and using the formula n = A/Re where A is a coefficient, dependent on the diffusion mechanism of the current carriers, R is the Hall constant and e is the electronic There are no accurate data for the change in A with However, estimated values are concentration of acceptor atoms. shown to give results within the limits of experimental error. The dependence of the specific resistance: ρ on the concentration of Al atoms n is also determined and shown to fall on the same line as values for In and for In, Al, Ga obtained previously. ρ varies from 5 x 10^{-2} to 2 x $10^{-\frac{1}{4}}$ ohm cm for n varying from 10^{17} to 10^{21} cm⁻³. Values of the Hall mobility are calculated and shown to agree with earlier results. A weak dependence of μ on the concentration of acceptors is found at a concentration of Al atoms \geqslant 10¹⁸ cm-3 which appears to be dependent on screening. There are 3 figures and 1 table.

SUBMITTED: May 31, 1961 Card 2/2

-37736

5/180/62/000/002/015/018 E040/E535

18.1200

AUTHORS:

Zemskov, V.S., Zhurkin, B.G. and Yurkina, K.V. (Moscow)

TITLE:

The solubility of arsenic in germanium

PERIODICAL: Akademiya nauk SSSR. Izvestiya. Otdeleniye

tekhnicheskikh nauk. Metallurgiya i toplivo, no.2,

1962, 134-135

TEXT: Arsenic is one of the most commonly used alloying elements of germanium but, in spite of this, the available technical data for the solubility of arsenic in germanium are incomplete and often conflicting. The present investigation was carried out using a technique involving the extraction of samples. from molten germanium solution containing various concentrations of arsenic and subsequent investigation, of the specimens thus obtained, by X-ray structural and microscopic analyses, determination of the quantity of current carriers from measurements of the Hall constant and measurement of the specimen resistivity at room temperature. The starting materials for the investigations were germanium with the resistivity @ = 35-40 ohm cm and diffusion length of the minority current carriers of not less than 2-2.5 mm. Card 1/2

The solubility of arsenic .

S/180/62/000/002/015/018 E040/E535

The arsenic contained calcium and magnesium impurities in concentrations not exceeding 10⁻³ and 10⁻¹%, respectively. A partial phase composition diagram for the As-Ge system is constructed in semi-logarithmic coordinates in the temperature range 700 - 937°C and the solidus line is drawn in, together with the liquidus line quoted on the basis of data reported by H. Stöhr and W. Klemm (Ref.6: Z.anorgan.und allgem.Chem., 1940, 244, p.205). It was established that the highest solubility of arsenic in germanium does not exceed 0.12 at.%. The above figure for the maximum solubility of arsenic in germanium-base solid solution agrees well with the value recently reported in the paper by P. L. Moody and A. J. Strauss (Ref.9: J. Electrochem.Soc., 1960, v.107, p.64). There are 1 figure and 1 table.

SUBMITTED: May 31, 1961

Card 2/2

S/076/62/036/009/003/011 B101/B102

AUTHORS:

Zemskov, V. S., Suchkova, A. D., and Zhurkin, B. G. (Moscow)

TITLE:

Study of the heterogeneous equilibrium in the system Ge-In-Sb

PERIODICAL: Zhurnal fizicheskoy khimii, v. 36, no. 9, 1962, 1914 - 1918

TEXT: The equilibrium between the solid and liquid phases was determined on three cross sections passing through the Ge-InSb cross section. The a - a cross section corresponded to a Ge content of 86.7 atomic, equilibrium temperature 860°C, the b - b cross section to a Ge content of 71 atomic, equilibrium temperature 812°C, and the c - c cross section to a Ge content of 41.2 atomic, equilibrium temperature 672°C. The concentration of admixtures (In, Sb) was determined in the Ge crystal pulled at 0.4 mm/min. n-type Ge was used, resistivity 30 ohin.cm, electron mobility 3600 cm/v.sec, diffusion length of minority carriers >2 mm. The crystals were examined radiographically, the number of carriers and the Hall constant were determined, and the macro- and microstructures were investigated. The Sb concentration was determined with the aid of Sb¹²⁴, the In concentration on the basis of the number of current carriers. Results: Card 1/V

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(Fig.): Solid phases containing more Sb than In are in equilibrium with the Ge-InSb cross section. Thus, the Ge - InSb cross section is not a quasibinary system as it does not reproduce the true equilibrium between the solid and liquid phases. The increased solubility of In and Sb jointly present in Ge is explained by an electron - hole equilibrium in the solid phase, since the formation of [InSb] complexes is improbable at the experimental temperature. There is 1 figure.

ASSOCIATION: Institut metallurgii im. A. A. Baykova (Institute of Metallurgy imeni A. A. Baykov)

SUBMITTED: January 7, 1961

Fig. Variation of the Sb and In contents in the solid phases as a function of their concentrations in the liquid phase. (a) = a - a cross section; (b) = b - b cross section; (c) = c - c cross section; (1) Sb in the solid phase; (2) In in the solid phase; ann = a tom; dotted line = theoretical solutility.

Card 2/0 >

ACCESSICI NR: AP3001278

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AUTHORS: Zemskov, V. S.; Helaya, A. D.

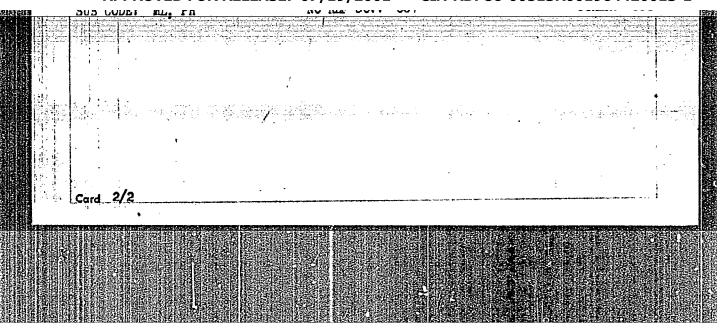
TITLE: Interaction of albumpum land anti-source desired artists.

TITLE: Interaction of aluminum and antizony during crystallisation of germanium from melts containing these elements

SCHRCE: Fizika twerdogo tela, v. 5, no. 6, 1963, 1601 - 1604

TOPIC TAGS: solid solution, Ge, Al, Sb, distribution coefficient

ABSTRACT: The authors have investigated the heterogeneous equilibrium in the three-member system Ge-Al-Sb. They studied solid solutions obtained from melts containing 97, 90, and 80 stomic & Ge with different Al-Sb ratios. They found qualitative support for earlier conclusions that a layer of Ge-AlSb does not reflect equilibrium between liquid and solid phases during crystallization of germanium melts according to the composition lying in this layer. The distribution coefficients of the elements show an interaction between atoms of the alloygin components during changes in the ratios of these alloying slements in a melt



ACCESSION NR: APLOLO989

3/0279/64/000/003/0154/0157

AUTHORS: Zemskov, V. S. (Moscow); Rozhdestvenskaya, V. V. (Moscow)

TITLE: Boron distribution during crystallization of solid solutions of germanium in silicon

SOURCE: AN SSSR. Izvestiya. Metallurgiya i gornoye delo, no. 3, 1964, 154-157

TOPIC TAGS: boron germanium, silicon, solid solution, semiconductor, doping, impurity content

ABSTRACT: The behavior of most doping components during crystallization of Ge and Si furnishes data on equilibrium coefficients of distribution depending on the concentration of the doping impurity in the melt. When the boron content is small in a melt (3°10¹⁸ cm⁻³), its effective coefficient of distribution is found to be 17 during crystallization of Ge, 0.8 during crystallization of Si. But there have been no studies on the interaction between doping impurities and Ge and Si during crystallization of solid solutions of these semiconductors to give a continuous series of solid solutions. The authors now furnish results of studies on the distribution of boron during crystallization of Ge-Si solutions containing boron.

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ACCESSION NR: AP4040989

Their experiments show that when the Ge content in melts is increased to 30%, the effective coefficient of boron distribution increases from less than one to values near one and higher. This coefficient depends on the concentration of boron in the solid phase, and when the concentration changes from 6.2.1018 to 4.4.1020 atm/cm³, it is almost halved, which indicates a change in ionization conditions of boron atoms in the solid phase. "The authors thank N. Kh. Abrikosov for his constant interest in the work and V. P. Dmitriyev for his aid in measuring the electrical conductivity." Orig. srt. has: 1 figure, 1 table, and 6 formulas.

ASSOCIATION: none

SUBMITTED: 09Sep63

ENCL: 00

SUB CODE: EC

NO REF SOV: OOL

other: 007

Card 2/2

ACCESSION NR: AP4043399

5/0181/64/006/008/2552/2554

AUTHORS: Zemskov, V. S.; Belaya, A. D.; Podkory*tova, G. N.

TITLE: On the electric activity of tin in germanium

SOURCE: Fizika tverdogo tela, v. 6, no. 8, 1964, 2552-2554

TOPIC TAGS: tin, germanium, doping, liquid phase, solid phase, distribution statistics, single crystal, Hall effect, electroneutral molecule, impurity conduction, ionization energy

ABSTRACT: In view of the contradictory data on this subject, the authors attempt to ascertain the electric activity of tin in germanium by employing a theory of H. Reiss (J. Chem. Phys., v. 21, 1209, 1953), from which it follows that when the ionization conditions of the doping atoms change, an accompanying change takes place in the distribution coefficients of these elements between the liquid and solid phase. Thus, if tin is a donor, then its addi-

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ACCESSION NR: AP4043399

tion to germanium doped with an acceptor element should cause an increase in the distribution coefficient of both the tin and of the acceptor element. The acceptor element employed was gallium. The germanium single crystals were grown by a procedure described in detail elsewhere (FTT, v. 5, 1601 and 1100, 1963). concentration was determined by Hall-effect measurements. tained data on the concentration of gallium and tin in the solid phase were used to calculate the distribution coefficients and to plot the dependence of the distribution coefficients of gallium and tin on the ratio of these elements in the liquid phase. results can be interpreted only by assuming that tin is not electrically neutral and that its donor nature is due to the unusual dependence of the distribution coefficient of gallium on its concentration in the melt. This explains also the disparity between the theoretically calculated and experimentally measured distribution coefficients of gallium, for the calculations were based on the assumption that the tin is electrically neutral. It is there-

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ACCESSION NR: AP4043399

fore concluded that tin serves as a donor impurity in germanium and that the ionization energy of the tin atoms is close to the ionization energy of the germanium. Orig. art. has: 1 figure.

ASSOCIATION: Institut metallurgii im. A. A. Baykova, Moscow (Institute of Metallurgy)

SUBMITTED: 02Mar64

ENCL: 01

SUB CODE: 65

NR REF SOV: 004

OTHER: 006

Card 3/4

ZEMSKOV, V.S.; SUCHKOVA, A.D.; ZHURKIN, B.G.

Heterogeneous equilibrium in the system Ge - In - Sb. Zhur. fiz. khim. 36 no.9:1914-1918 S '62. (MIRA 17:6)

1. Institut metallurgii imeni A.A. Boykova, Moskva.

GLAZOV, V.M.; ZIMSKOV, V.S.; ZHIRKIN, B.G.; SUCHKOVA, A.D.; LYU CHZHEN!-YUAN! [Liu Chen-yuan]

Physicochemical analysis of systems Ge(Si) - A^{II} -B^V. Trudy Inst. met. no.14:108-119 '63 (MJRA 17:8)

ZEMSKOV, V.S. (Moskva); ROZHDESTVENSKAYA, V.V. (Moskva)

Nestribution of boron during the crystallimation of solii solutions of germanium in silicon. Izv. AN SEAR Met. 1 gov. delo no.32154-158 My-Jeff. (MDRA 1727)

ZEMSKOV, V.S.; BELAYA, A.D.; PODKORYTOVA, G.N.

Electric activity of tin in germanium. Fiz. tver. tela 6 no.8: 2552-2554 Ag 164. (MIRA 17:11)

1. Institut metallurgii imeni Baykova, Moskva.

ZEMSKOV, V.S.

Phosphorus vapor pressure over a silicon melt alloyed with phosphorus. Izv. AN SSSR. Neorg. mat. 1 no.5:648-654 My '65. (MIRA 18:10)

1. Institut metallurgii imeni Baykova.